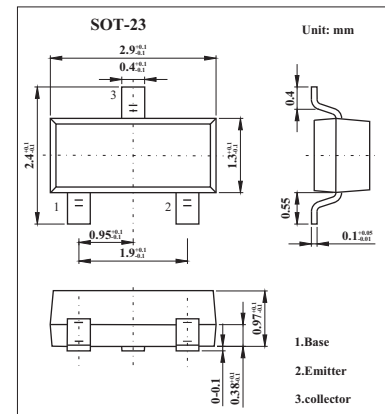


## Epitaxial Planar PNP Transistor

### KTA1504S-Y

#### ■ Features

- Collector Power Dissipation:  $P_c=150\text{mW}$
- Collector Current:  $I_c=-150\text{mA}$



#### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Collector-Base Voltage	$V_{CBO}$	-50	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_c$	-150	mA
Collector Power Dissipation	$P_c$	150	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	$^\circ\text{C}$

#### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_c=-100\mu\text{A}, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_c=-1\text{mA}, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu\text{A}, I_c=0$	-5			V
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=-50\text{V}, I_E=0$			-0.1	$\mu\text{A}$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=-5\text{V}, I_c=0$			-0.1	$\mu\text{A}$
DC Current Gain	$h_{FE}$	$V_{CE}=-6\text{V}, I_c=-2\text{mA}$	120		240	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=-100\text{mA}, I_B=-10\text{mA}$		-0.1	-0.3	V
Transition Frequency	$f_T$	$V_{CE}=-10\text{V}, I_c=-1\text{mA}$	80			MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		4.0	7.0	pF
Noise Figure	NF	$V_{CE}=-6\text{V}, I_c=-0.1\text{mA}, f=1\text{kHz}, R_g=10\text{K}\Omega$		1.0	10	dB